

MOSFET - Power, Single N-Channel, SO8-FL 25 V, 0.68 mΩ, 380 A

Product Preview

NTMFS0D8N02P1E

Features

- Small Footprint (5x6mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DS}	25	V	
Gate-to-Source Voltage		V_{GS}	+16/ -12	V	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D	380	A
		$T_C = 85^\circ\text{C}$		274	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^\circ\text{C}$	P_D	139	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	68	A
		$T_A = 85^\circ\text{C}$		42	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		$T_A = 25^\circ\text{C}$	P_D	3.2	W
Continuous Drain Current $R_{\theta JA}$ (Notes 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	31	A
		$T_A = 85^\circ\text{C}$		22	
Power Dissipation $R_{\theta JA}$ (Notes 2, 3)		$T_A = 25^\circ\text{C}$	P_D	0.93	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	TBD	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = \text{TBD } A_{pk}, L = 0.1 \text{ mH}$) (Note 4)		E_{AS}	TBD	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in² pad size, 2 oz Cu pad.
2. Surface-mounted on FR4 board using minimum pad size, 2 oz Cu pad.
3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted. Actual continuous current will be limited by thermal & electro-mechanical application board design. $R_{\theta JC}$ is determined by the user's board design.
4. 100% UIS tested at $L = 1 \text{ mH}, I_{AS} = 30.7 \text{ A}$.

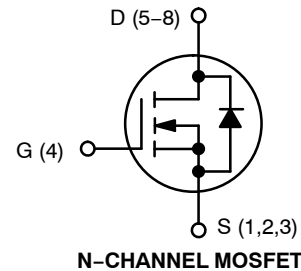
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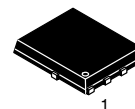
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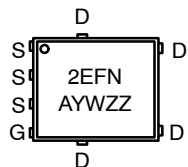
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
25 V	0.68 mΩ @ 10 V	380 A
	0.84 mΩ @ 4.5 V	



MARKING DIAGRAMS



SO-8 FLAT LEAD
CASE 488AA
STYLE 1



2EFN = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	0.9	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	39	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	135	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$, ref to 25°C		16		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$			10	μA
		$T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = +16\text{ V}/-12\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 2\text{ mA}$	1.2		2.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 2\text{ mA}$, ref to 25°C		-4.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 46\text{ A}$		0.44	0.68	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 43\text{ A}$		0.54	0.84	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 46\text{ A}$		307		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$		0.48		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 13\text{ V}, f = 1\text{ MHz}$		8600		pF
Output Capacitance	C_{OSS}			2285		
Reverse Transfer Capacitance	C_{RSS}			129		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 13\text{ V}; I_D = 46\text{ A}$		52		nC
Threshold Gate Charge	$Q_{G(TH)}$			10		
Gate-to-Source Charge	Q_{GS}			8.9		
Gate-to-Drain Charge	Q_{GD}			21		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 13\text{ V}; I_D = 46\text{ A}$		116		nC

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 13\text{ V}, I_D = 46\text{ A}, R_G = 6.0\ \Omega$		45		ns
Rise Time	t_r			24		
Turn-Off Delay Time	$t_{d(OFF)}$			68		
Fall Time	t_f			20		

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 13\text{ V}, I_D = 46\text{ A}, R_G = 6.0\ \Omega$		23		ns
Rise Time	t_r			6.8		
Turn-Off Delay Time	$t_{d(OFF)}$			123		
Fall Time	t_f			19		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 46\text{ A}$	$T_J = 25^\circ\text{C}$		0.77	1.2	V
			$T_J = 125^\circ\text{C}$		0.62		

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 46 A		64		ns
Reverse Recovery Charge	Q _{RR}			87		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping†
NTMFS0D8N02P1ET1G	2EFN	DFN5 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

